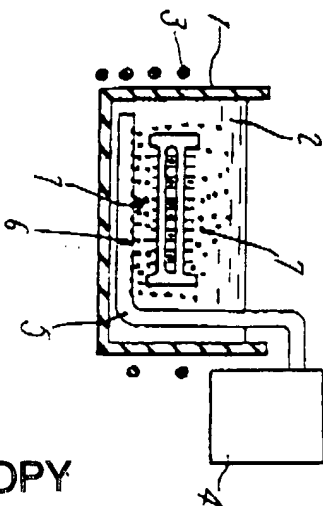


(54) WASHING METHOD FOR SILICON WAFER

- (11) Kokai No. 54-34751 (43) 3.14.1979 (19) JP
 (21) Appl. No. 52-100473 (22) 8.24.1977
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 (52) JPC: 99(5)A04:99(5)C3
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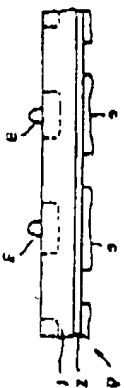
PURPOSE: To oxidize and remove foreign matter on a Si substrate surface while supplying O_3 into a washing solution.

CONSTITUTION: By heating NH_4OH up to $150^\circ C$, bubbles 7 of O_3 are made to come out from apertures 6 of tube 5 at the bottom. Next, jig 9 in which Si substrate 8 is installed is dipped for about ten minutes. At this time, the supply of O_3 is maintained constant. Therefore, much O_3 touches the substrate to increase the washing effect, and when the density of NH_3 in the washing solution is between 5 and 20%, the washing effect is highest.



(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

- (11) Kokai No. 54-34752 (43) 3.14.1979 (19) JP
 (21) Appl. No. 52-101877 (22) 8.24.1977
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